L Number	Hits	Search Text	DB	Time stamp
2	1350	(257/777).CCLS.	USPAT;	2004/10/27 16:54
' I			US-PGPUB;	,
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	2613	257/777	USPĀT;	2004/10/27 16:55
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
4	4196	257/778	IBM_TDB USPAT;	2004/10/27 17:12
4	4196	231/118	US-PGPUB;	2004/10/2/ 17:12
			EPO; JPO;	
			DERWENT;	
		•	IBM TDB	
5	1743	257/779	USPAT;	2004/10/27 17:30
-	_		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	2057	257/780	USPAT;	2004/10/27 17:45
			US-PGPUB;	
]			EPO; JPO;	
		•	DERWENT;	
7	1063	257/781	IBM_TDB USPAT;	2004/10/27 18:03
'	1063	257/781	US-PGPUB;	2004/10/2/ 18:03
1			EPO; JPO;	•
,			DERWENT;	
			IBM TDB	
8	4196	257/778	USPĀT;	2004/10/27 18:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	3831	257/723	USPAT;	2004/10/27 18:12
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
10	1		USPAT	2004/10/27 18:06
11	1		USPAT	2004/10/27 18:07
12	ī		USPAT	2004/10/27 18:07
13	2661	257/724	USPAT;	2004/10/27 18:30
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		058/505	IBM_TDB	0004/10/07 10 17
14	1209	257/685	USPAT;	2004/10/27 18:47
			US-PGPUB; EPO; JPO;	
			DERWENT;	
		,	IBM TDB	
15	2825	257/686	USPAT;	2004/10/27 19:06
	2025		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	2768	257/690	USPĀT;	2004/10/27 19:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
12	2	/	IBM_TDB	2004/10/07 22 22
17	3612	(semiconductor or die or chip or Ic) with	USPĀT	2004/10/27 22:23
		wir\$3 and solder near (ball or bump) and		
18	487	<pre>(encapsulat\$3 or mold\$3) ((semiconductor or die or chip or Ic) with</pre>	USPAT	2004/10/27 22:24
10	40/	wir\$3 and solder near (ball or bump) and	OSEKI	2,004/10/2/ 22:24
		(encapsulat\$3 or mold\$3) ) and (ball or		
		bump) with (big or large)		
	<del></del>	<u>, , , , , , , , , , , , , , , , , , , </u>	<del></del>	1

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19	2749	257/700	USPAT;	2004/10/27 20:00
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
20	2211	438/108	USPAT;	2004/10/27 20:25
20	2211	4307 100	US-PGPUB;	2001/10/2/ 20120
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
21	37	"5844315"	USPĀT	2004/10/27 20:12
22	1		USPAT	2004/10/27 20:09
23	1		USPAT	2004/10/27 20:09
24	1		USPAT	2004/10/27 20:09
25	1		USPAT	2004/10/27 20:09
26	1		USPAT	2004/10/27 20:09
27	1		USPAT	2004/10/27 20:09
28	1 1		USPAT USPAT	2004/10/27 20:09 2004/10/27 20:10
30	1		USPAT	2004/10/27 20:10
31	1		USPAT	2004/10/27 20:11
32	35	"5608265"	USPAT	2004/10/27 20:12
33	1045	438/109	USPAT;	2004/10/27 20:42
• •			US-PGPUB;	
		·	EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
34	3850	361/760	USPĀT;	2004/10/27 21:34
			US-PGPUB;	
			EPO; JPO;	'
			DERWENT;	
		100	IBM_TDB USPAT	2004/10/27 21:40
37	0	stack\$3 near (semiconductor or chip or	USPAT	2004/10/2/ 21:40
		die) and (lower or bottom) near (semiconductor or chip or die) with memory		
ļ		and (upper or top) near (semiconductor or		
		chip or die) with microprocessor.		
38	0	(lower or bottom) near (semiconductor or	USPAT	2004/10/27 21:36
		chip or die) with memory and (upper or		
		top) near (semiconductor or chip or die)		
		with microprocessor.		
39	0	stack\$3 near (semiconductor or chip or	USPAT	2004/10/27 21:37
		die) and (semiconductor or chip or die)		
		near memory and (semiconductor or chip or		
1	_	die) near microprocessor.	HODAM	2004/10/27 01:20
40	0	stack\$3 near (semiconductor or chip or	USPAT	2004/10/27 21:39
	1	die) and (semiconductor or chip or die) with memory and (semiconductor or chip or		
1		die) with microprocessor.		
41	0	257/777 and (semiconductor or chip or	USPAT	2004/10/27 21:37
1 1		die) with memory and (semiconductor or		
		chip or die) with microprocessor.		
42	0	(semiconductor or chip or die) with	USPAT	2004/10/27 21:37
		memory and (semiconductor or chip or die)		
		with microprocessor.		
43	0	(semiconductor or chip or die) with	USPAT	2004/10/27 21:38
		memor\$3 and (semiconductor or chip or die)		
		with micro near processor.	II C D A M	2004/10/27 21:39
44	0	(semiconductor or chip or die or IC) with	USPAT	2004/10/2/ 21:39
1	1	memor\$3 and (semiconductor or chip or die or IC) with microprocessor.		
45	91434	(semiconductor or chip or die or IC) with	USPAT	2004/10/27 21:38
••	51,353	memor\$3		
46	0	l	USPAT	2004/10/27 21:39
	1	microprocessor.		
47	0	t	USPAT	2004/10/27 21:39
		micro near processor.		l
48	0	[ (	USPAT	2004/10/27 21:39
1		micro-processor.		0004/10/07 04 55
49	22456	•	USPAT	2004/10/27 21:39
	<u>L</u>	microprocessor	L	1

die) and (semiconductor or chip or die) with memory and (semiconductor or chip or die) with microprocessor  51  0 stack\$3 near (semiconductor or chip or die) and (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  52  5 (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  64  0 ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large) (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)	F0 1	100	1 +	HODE	10004/10/07 01 40
with memory and (semiconductor or chip or die) with microprocessor  51 0 stack\$3 near (semiconductor or chip or die) and (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  52 5 (lower or bottom) near (semiconductor or chip or die) with microprocessor  54 0 ((semiconductor or die or chip or die) with microprocessor  55 0 ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  55 0 104 (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  55 0 104 (lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor or chip or die) with microprocessor) and (semiconductor or chip or die) with microprocessor) and (semiconductor	30	188	_ · · · · · · · · · · · · · · · · · · ·	USPAT	2004/10/27 21:40
die) with microprocessor  stack\$3 near (semiconductor or chip or die) and (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  [lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or die) with microprocessor  [lower or bottom) near (semiconductor or die) with microprocessor  [lower or bottom) near (semiconductor or die) with microprocessor  [lower or die) with memory and (upper or die) with microprocessor  [lower or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) and (ball or bump) with (big or large)  [lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor or die) with microprocessor) and (semiconductor or die) with microprocessor) and (semiconductor or die)					
51 0 stack\$3 near (semiconductor or chip or die) and (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor ((semiconductor or chip or die) with microprocessor ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) and (ball or bump) with (big or large) (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor					
die) and (lower or bottom) near					
(semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor	51	0		USPAT	2004/10/27 21:40
and (upper or top) near (semiconductor or chip or die) with microprocessor  (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) and (ball or bump) with (big or large)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor			l '		ļ i
chip or die) with microprocessor  (lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)) and (ball or bump) with (big or large)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor or die) with microprocessor) and (semiconductor					
52					
chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor)  USPAT  2004/10/27 22:  USPAT  2004/10/27 22:					
top) near (semiconductor or chip or die) with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large) (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor	52	5	, ·	USPAT	2004/10/27 22:45
with microprocessor  ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor)  with microprocessor) and (semiconductor)			chip or die) with memory and (upper or	•	
0 ((semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  104 (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  55 5 ((lower or bottom) near (semiconductor or chip or die) with microprocessor) and (semiconductor)  USPAT 2004/10/27 22:  2004/10/27 22:  2004/10/27 22:			top) near (semiconductor or chip or die)		
wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  104 (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  55 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			with microprocessor		
(encapsulat\$3 or mold\$3) ) and (ball or bump) with (big or large)  104 (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  55 5 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor	54	0	((semiconductor or die or chip or Ic) with	JPO	2004/10/27 22:24
bump) with (big or large) (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3) ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			wir\$3 and solder near (ball or bump) and		
104 (semiconductor or die or chip or Ic) with wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  55 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			(encapsulat\$3 or mold\$3) ) and (ball or		
wir\$3 and solder near (ball or bump) and (encapsulat\$3 or mold\$3)  5 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			bump) with (big or large)		
(encapsulat\$3 or mold\$3) 55 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor	53	104	(semiconductor or die or chip or Ic) with	JPO	2004/10/27 22:24
55 ((lower or bottom) near (semiconductor or chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			wir\$3 and solder near (ball or bump) and		
chip or die) with memory and (upper or top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			(encapsulat\$3 or mold\$3)		
top) near (semiconductor or chip or die) with microprocessor) and (semiconductor	55	5	((lower or bottom) near (semiconductor or	USPAT	2004/10/27 22:46
top) near (semiconductor or chip or die) with microprocessor) and (semiconductor			chip or die) with memory and (upper or		
with microprocessor) and (semiconductor					
			• ·		
(semiconductor or chip or die) with					
microprocessor			- ·		